



24N60-CB

Power MOSFET

24A, 600V N-CHANNEL POWER MOSFET

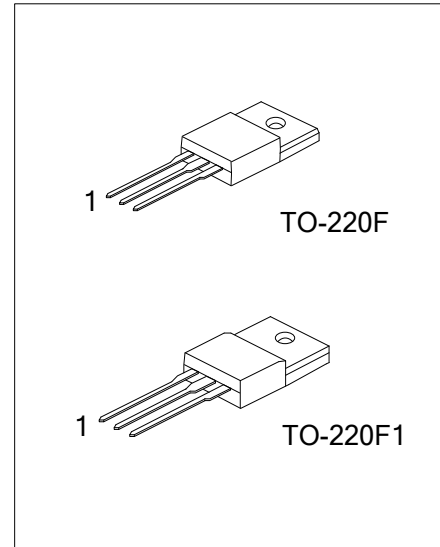
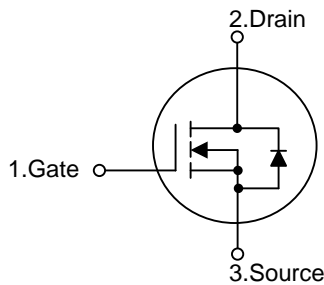
DESCRIPTION

The UTC **24N60-CB** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \leq 0.31 \Omega @ V_{GS}=10V, I_D=12A$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL



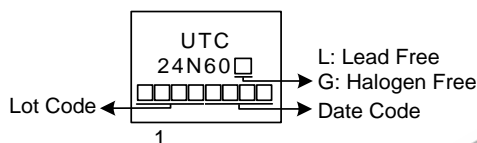
ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|----------|----------------|---|---|---------|
| Lead Free | Halogen-Free | | 1 | 2 | 3 | |
| 24N60L-TF1-T | 24N60G-TF1-T | TO-220F1 | G | D | S | Tube |
| 24N60L-TF3-T | 24N60G-TF3-T | TO-220F | G | D | S | Tube |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|--|--|
| | <p>(1) T: Tube</p> <p>(2) TF1: TO-220F1, TF3: TO-220F</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p> |
|--|--|

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------------|------------------------|-----------------|------|
| Drain-Source Voltage | V _{DSS} | 600 | V |
| Gate-Source Voltage | V _{GSS} | ±30 | V |
| Drain Current | Continuous | I _D | 24 |
| | Pulsed (Note 2) | I _{DM} | 48 |
| Avalanche Energy | Single Pulsed (Note 3) | E _{AS} | 205 |
| Peak Diode Recovery dv/dt | dv/dt | 1.2 | V/ns |
| Power Dissipation | P _D | 32 | W |
| Junction Temperature | T _J | +150 | °C |
| Storage Temperature | T _{STG} | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 10mH, I_{AS} = 6.4A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

4. I_{SD} ≤ 24A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|-----------------|---------|------|
| Junction to Ambient | θ _{JA} | 62.5 | °C/W |
| Junction to Case | θ _{JC} | 3.9 | °C/W |

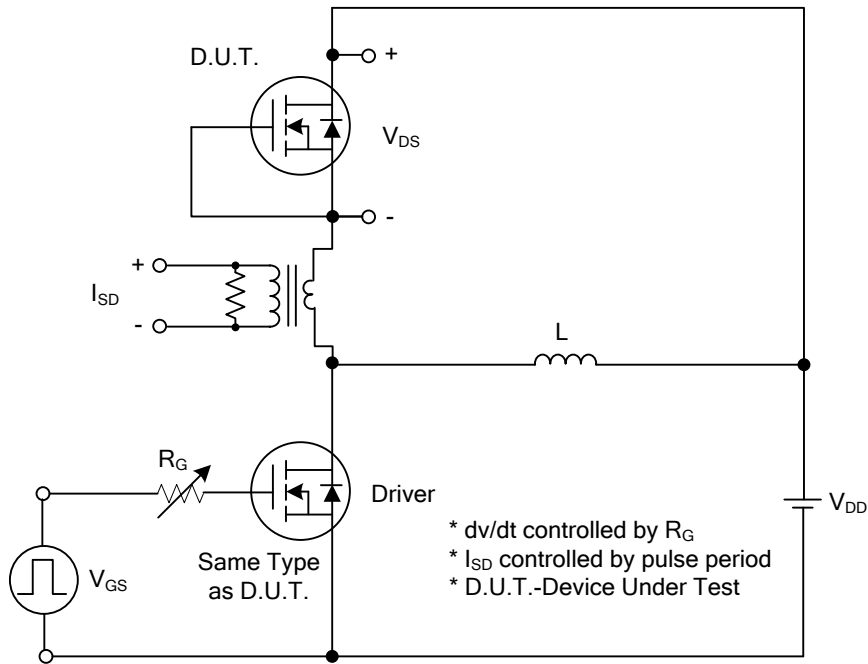
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---------------------|---|--|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | I _D =250μA, V _{GS} =0V | 600 | | | V |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =600V, V _{GS} =0V | | | 10 | μA |
| Gate- Source Leakage Current | I _{GSS} | Forward | | | +100 | nA |
| | | Reverse | V _{GS} =+30V, V _{DS} =0V | | | -100 |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | V _{DS} =V _{GS} , I _D =250μA | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =12A | | | 0.31 | Ω |
| DYNAMIC PARAMETERS | | | | | | |
| Input Capacitance | C _{ISS} | V _{GS} =0V, V _{DS} =25V, f=1MHz | | 4050 | | pF |
| Output Capacitance | C _{OSS} | | | 360 | | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | 13 | | pF |
| SWITCHING PARAMETERS | | | | | | |
| Total Gate Charge | Q _G | V _{DS} =480V, V _{GS} =10V, I _D =24A I _G = 1mA (Note1, 2) | | 73 | | nC |
| Gate to Source Charge | Q _{GS} | | | 16 | | nC |
| Gate to Drain Charge | Q _{GD} | | | 13 | | nC |
| Turn-ON Delay Time | t _{D(ON)} | V _{DS} =100V, V _{GS} =10V, I _D =24A, R _G =25Ω (Note1, 2) | | 16 | | ns |
| Rise Time | t _R | | | 16 | | ns |
| Turn-OFF Delay Time | t _{D(OFF)} | | | 45 | | ns |
| Fall-Time | t _F | | | 17 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Maximum Body-Diode Continuous Current | I _S | | | | 24 | A |
| Maximum Body-Diode Pulsed Current | I _{SM} | | | | 48 | A |
| Drain-Source Diode Forward Voltage | V _{SD} | I _S =24A, V _{GS} =0V | | | 1.4 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _S =24A, V _{GS} =0V, | | 500 | | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | di _F /dt=100A/μs (Note 1) | | 5.9 | | μC |

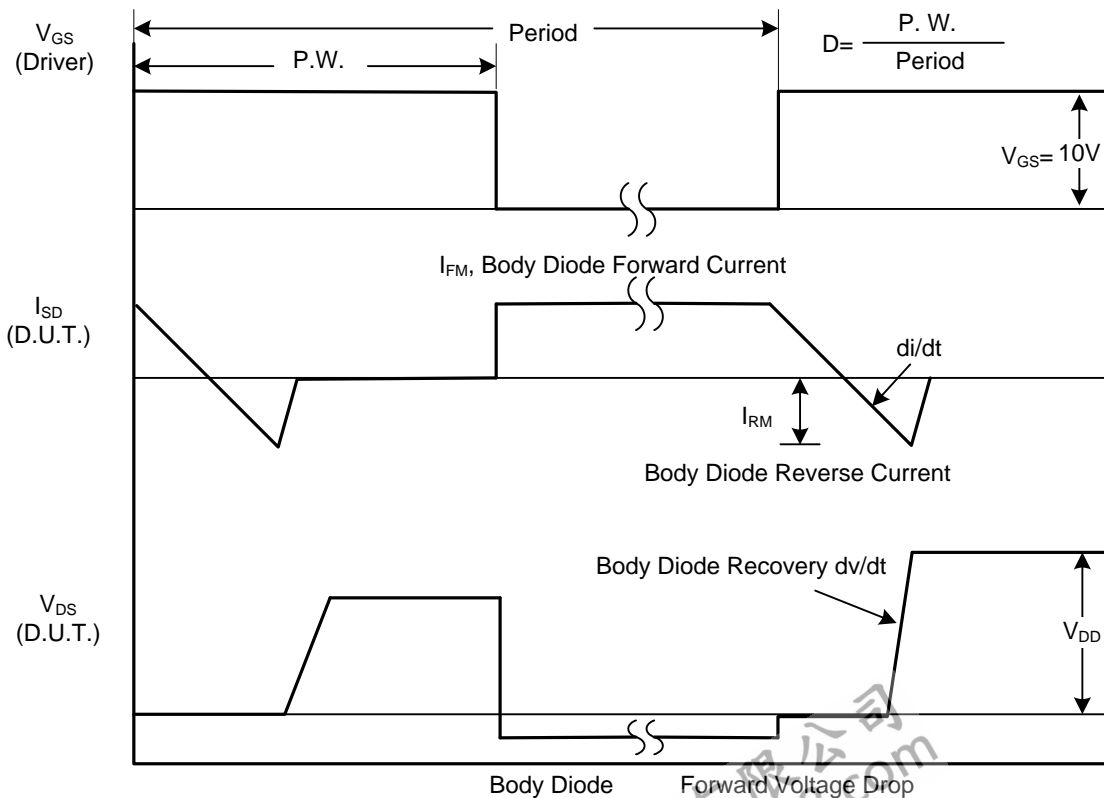
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating ambient temperature.

TEST CIRCUITS AND WAVEFORMS

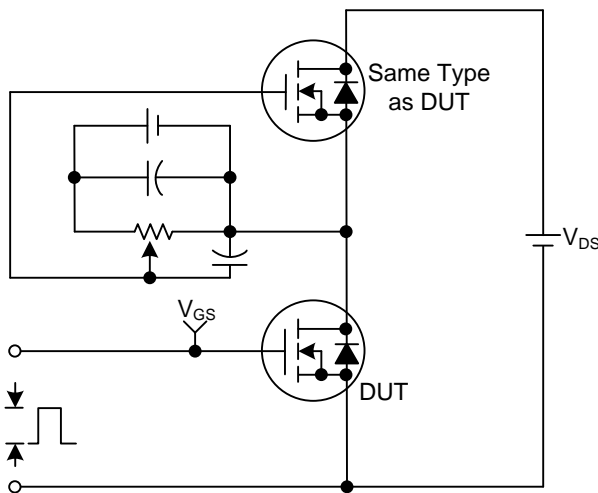


Peak Diode Recovery dv/dt Test Circuit

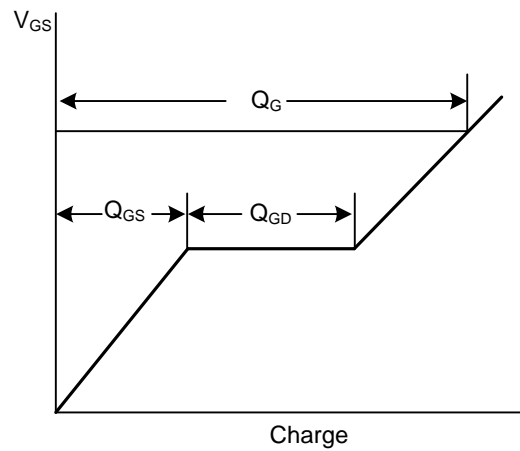


Peak Diode Recovery dv/dt Waveforms

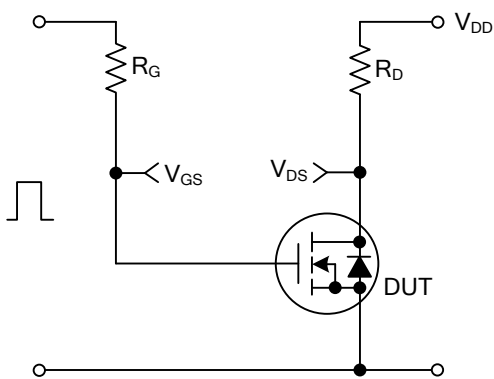
TEST CIRCUITS AND WAVEFORMS



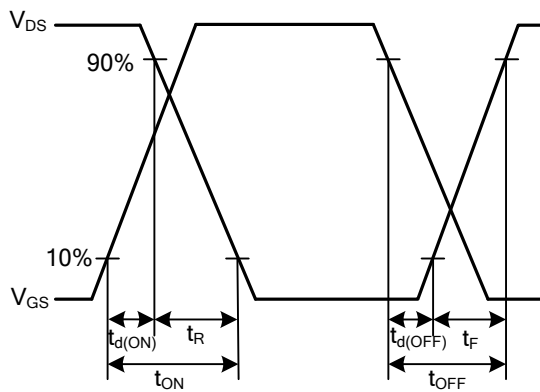
Gate Charge Test Circuit



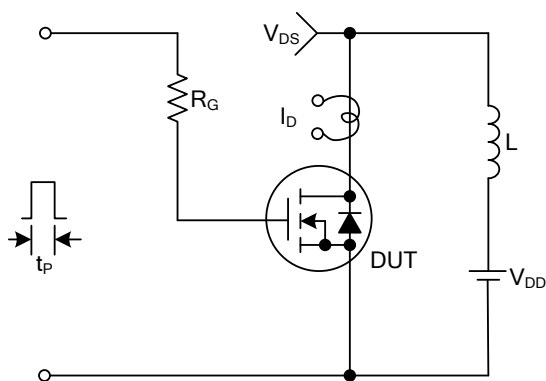
Gate Charge Waveforms



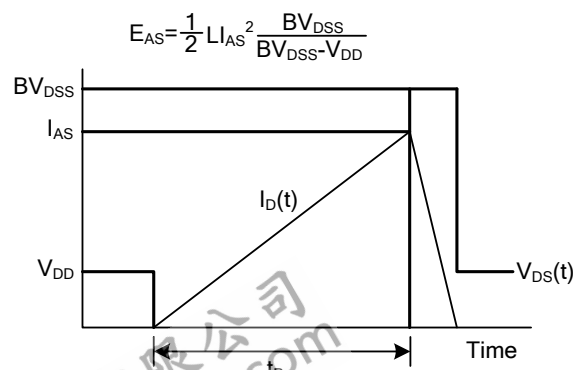
Resistive Switching Test Circuit



Resistive Switching Waveforms

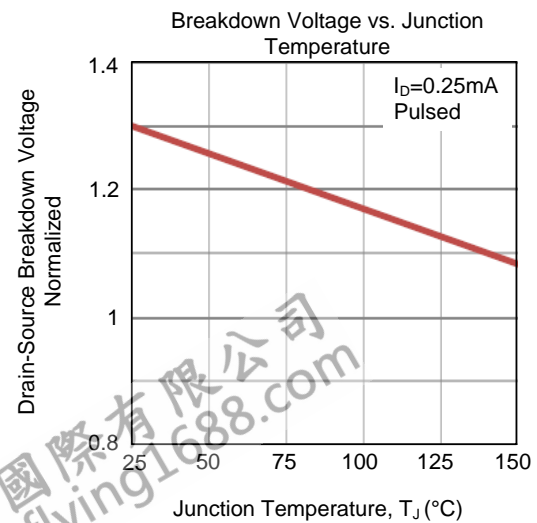
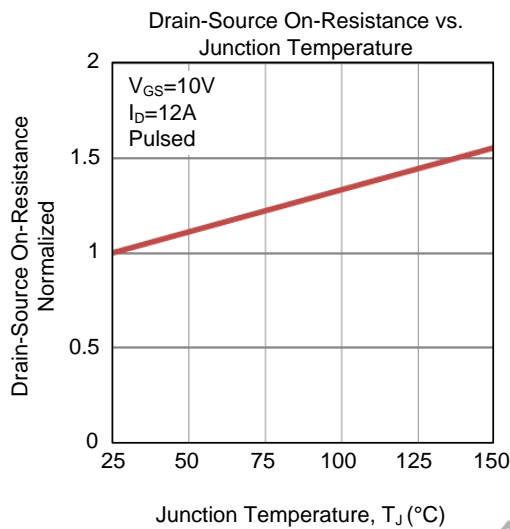
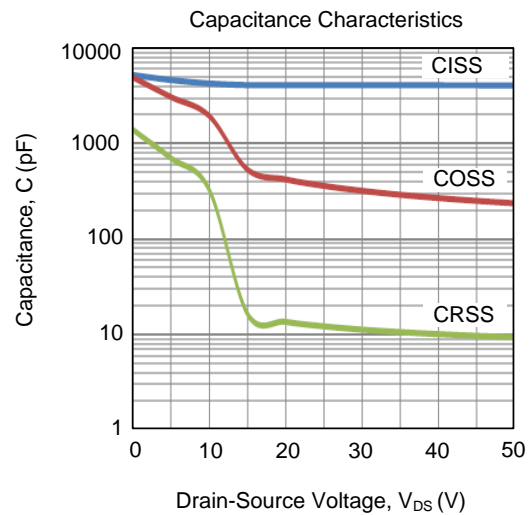
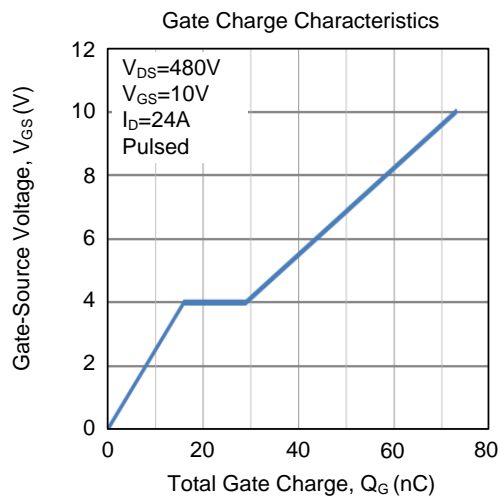
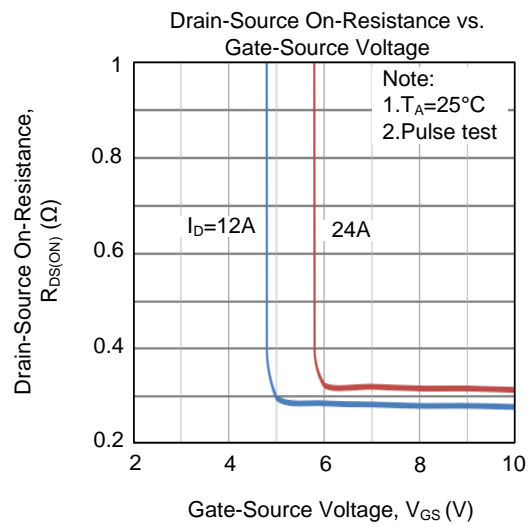
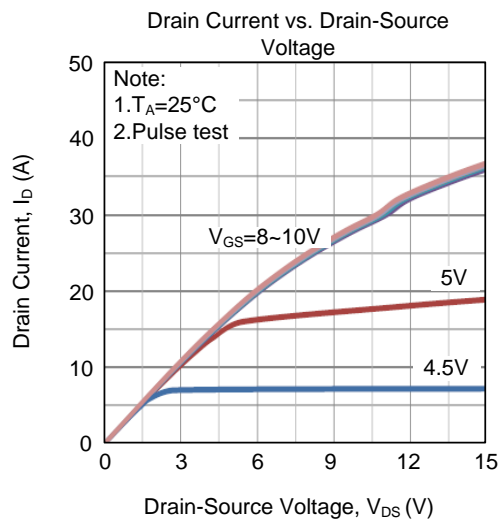


Unclamped Inductive Switching Test Circuit

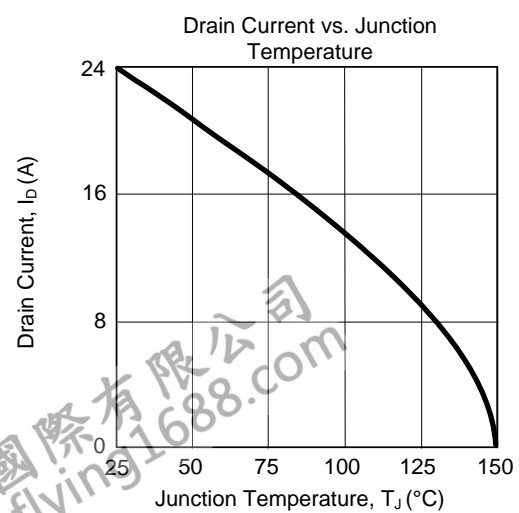
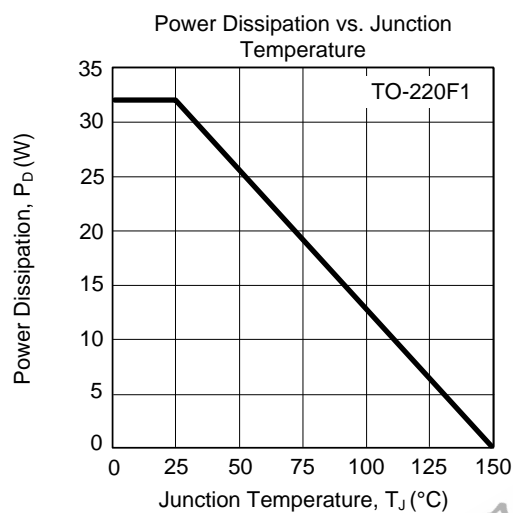
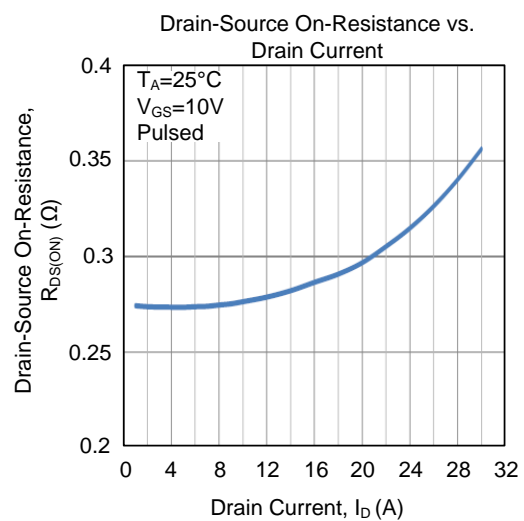
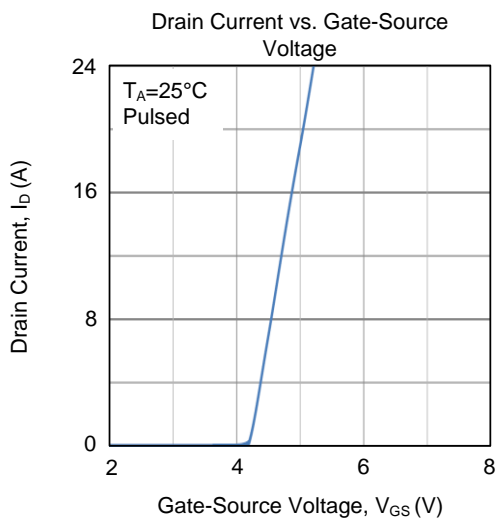
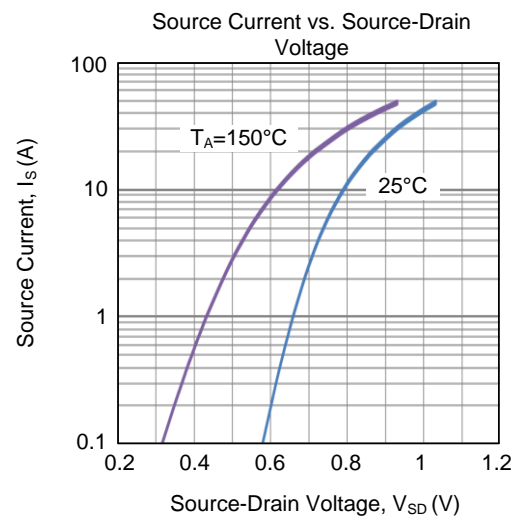
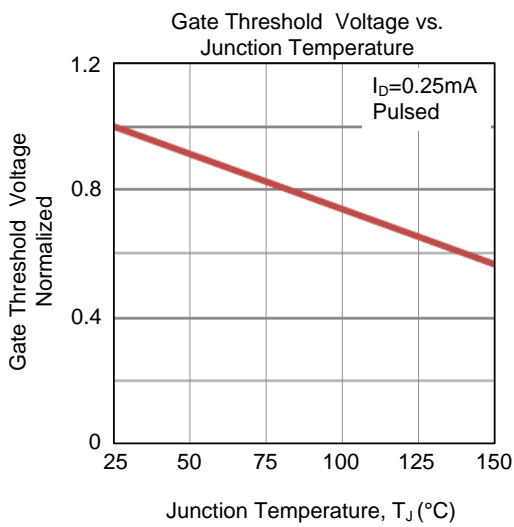


Unclamped Inductive Switching Waveforms

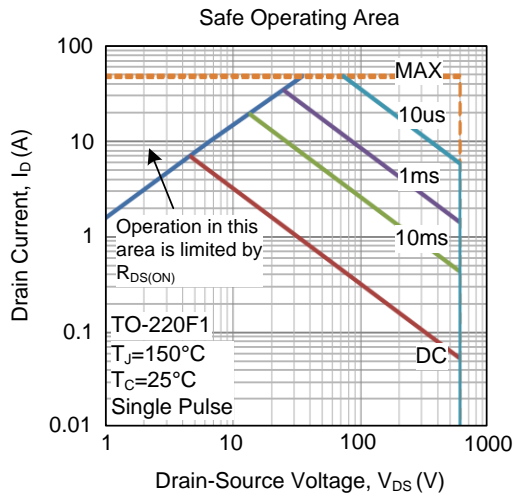
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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